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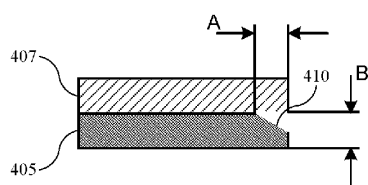


FIG. 4

(57) Abstract: Exemplary methods of forming semiconductor structures may include forming a silicon oxide layer from a silicon-containing precursor and an oxygen-containing precursor. The methods may include forming a silicon nitride layer from a silicon-containing precursor, a nitrogen-containing precursor, and an oxygen-containing precursor. The silicon nitride layer may be characterized by an oxygen concentration greater than or about 5 at.%. The methods may also include repeating the forming a silicon oxide layer and the forming a silicon nitride layer to produce a stack of alternating layers of silicon oxide and silicon nitride.

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